

# NCEP0190G

# **NCE N-Channel Super Trench Power MOSFET**

#### **Description**

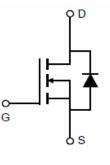
The NCEP0190G uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **General Features**

- $V_{DS}$  =100V, $I_D$  =90A  $R_{DS(ON)}$ =7.0m $\Omega$  (typical) @  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

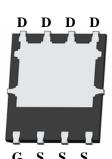
#### **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification









**Top View** 

**Bottom View** 

100% UIS TESTED!

100% AVds TESTED!

#### **Package Marking and Ordering Information**

| Device Marking | Device    | Device Package | Reel Size | Tape width | Quantity |
|----------------|-----------|----------------|-----------|------------|----------|
| NCEP0190G      | NCEP0190G | DFN5X6-8L      | -         | -          | -        |

#### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

| Parameter  | Symbol                | Limit      | Unit                   |  |
|--|-----------------------|------------|------------------------|--|
| Drain-Source Voltage                             | V <sub>DS</sub>       | 100        | V                      |  |
| Gate-Source Voltage                              | V <sub>G</sub> S      | ±20        | V                      |  |
| Drain Current-Continuous                         | I <sub>D</sub>        | 90         | Α                      |  |
| Drain Current-Continuous(T <sub>C</sub> =100 °C) | I <sub>D</sub> (100℃) | 63.6       | Α                      |  |
| Pulsed Drain Current                             | I <sub>DM</sub>       | 360        | А                      |  |
| Maximum Power Dissipation                        | P <sub>D</sub>        | 135        | W                      |  |
| Derating factor                                  |                       | 1.08       | W/℃                    |  |
| Single pulse avalanche energy (Note 5)           | E <sub>AS</sub>       | 460        | mJ                     |  |
| Operating Junction and Storage Temperature Range | $T_{J}$ , $T_{STG}$   | -55 To 150 | $^{\circ}\!\mathbb{C}$ |  |



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# **Thermal Characteristic**

| Thermal Resistance,Junction-to-Case <sup>(Note 2)</sup> | $R_{	heta JC}$ | 0.9 | °C/W |  |
|---|----------------|-----|------|--|
|---|----------------|-----|------|--|

Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

| Parameter                          | Symbol   | Condition                                   | dition Min T |      | Typ Max | Unit |
|------------------------------------|--|---|--------------|------|---------|------|
| Off Characteristics                |  |   |              |      |         |      |
| Drain-Source Breakdown Voltage     | BV <sub>DSS</sub>                                      | V <sub>GS</sub> =0V I <sub>D</sub> =250μA   |              | 108  | -       | V    |
| Zero Gate Voltage Drain Current    | I <sub>DSS</sub>                                       | V <sub>DS</sub> =100V,V <sub>GS</sub> =0V   | -            | -    | 1       | μΑ   |
| Gate-Body Leakage Current          | ody Leakage Current I <sub>GSS</sub> V <sub>GS</sub> = |   | -            | -    | ±100    | nA   |
| On Characteristics (Note 3)        |  |   |              |      |         |      |
| Gate Threshold Voltage             | V <sub>GS(th)</sub>                                    | $V_{DS}=V_{GS}$ , $I_{D}=250\mu A$          | 2.7          | 3.2  | 3.7     | V    |
| Drain-Source On-State Resistance   | R <sub>DS(ON)</sub>                                    | V <sub>GS</sub> =10V, I <sub>D</sub> =20A   | -            | 7.0  | 7.5     | mΩ   |
| Forward Transconductance           | <b>g</b> FS  | V <sub>DS</sub> =5V,I <sub>D</sub> =20A     | -            | 50   | -       | S    |
| Dynamic Characteristics (Note4)    |  |   |              |      |         |      |
| Input Capacitance                  | C <sub>lss</sub>                                       | \/ -50\/\/ -0\/                             | -            | 3458 | -       | PF   |
| Output Capacitance                 | Coss   | $V_{DS}$ =50V, $V_{GS}$ =0V,                | -            | 423  | -       | PF   |
| Reverse Transfer Capacitance       | C <sub>rss</sub>                                       | F=1.0MHz                                    | -            | 12.5 | -       | PF   |
| Switching Characteristics (Note 4) |  |   | •            | •    |         |      |
| Turn-on Delay Time                 | t <sub>d(on)</sub>                                     |   | -            | 13   | -       | nS   |
| Turn-on Rise Time                  | t <sub>r</sub>   | $V_{DD}$ =50 $V$ , $I_D$ =20 $A$            | -            | 4    | -       | nS   |
| Turn-Off Delay Time                | t <sub>d(off)</sub>                                    | $V_{GS}$ =10 $V$ , $R_{G}$ =3 $\Omega$      | -            | 26   | -       | nS   |
| Turn-Off Fall Time                 | t <sub>f</sub>   |   | -            | 4.5  | -       | nS   |
| Total Gate Charge                  | Qg   | V -F0V/I -20A                               | -            | 45   | -       | nC   |
| Gate-Source Charge                 | Q <sub>gs</sub>  | V <sub>DS</sub> =50V,I <sub>D</sub> =20A,   | -            | 15   |         | nC   |
| Gate-Drain Charge                  | Q <sub>gd</sub>  | V <sub>GS</sub> =10V                        | -            | 7    |         | nC   |
| Drain-Source Diode Characteristics |  |   |              |      |         |      |
| Diode Forward Voltage (Note 3)     | $V_{SD}$   | V <sub>GS</sub> =0V,I <sub>S</sub> =20A     | -            |      | 1.2     | V    |
| Diode Forward Current (Note 2)     | Is   |   | -            | -    | 90      | Α    |
| Reverse Recovery Time              | t <sub>rr</sub>  | T <sub>J</sub> = 25°C, I <sub>F</sub> = 20A | -            | 20   | -       | nS   |
| Reverse Recovery Charge            | Qrr  | $di/dt = 500A/\mu s^{(Note3)}$              | -            | 185  | -       | nC   |

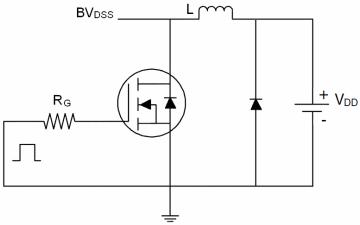
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,VDD=20V,VG=10V,L=0.5mH,Rg=25 $\Omega$

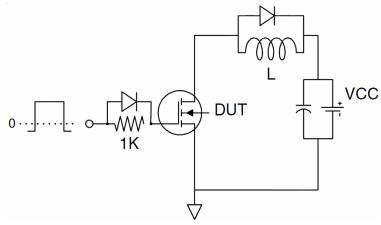


#### **Test Circuit**

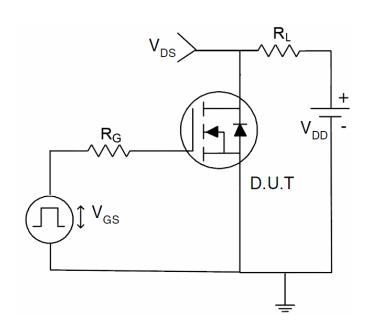
# 1) E<sub>AS</sub> test Circuit



# 2) Gate charge test Circuit



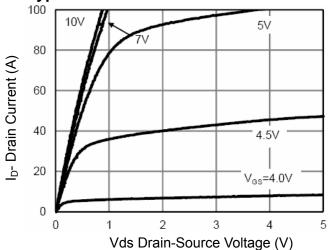
# 3) Switch Time Test Circuit



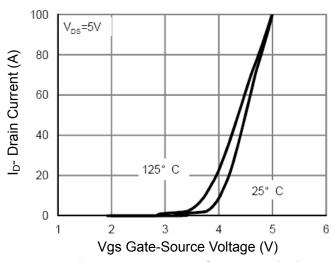
**Pb Free Product** 



### **Typical Electrical and Thermal Characteristics**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

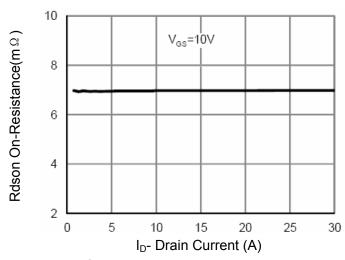
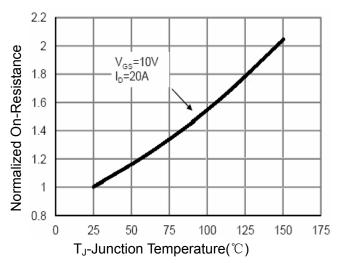


Figure 3 Rdson- Drain Current



**Figure 4 Rdson-Junction Temperature** 

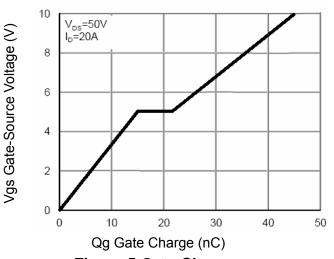


Figure 5 Gate Charge

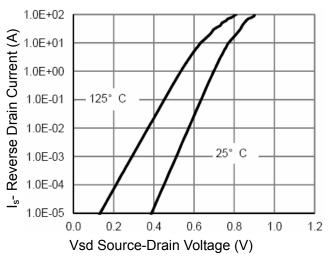


Figure 6 Source- Drain Diode Forward





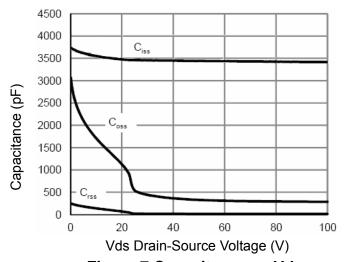


Figure 7 Capacitance vs Vds

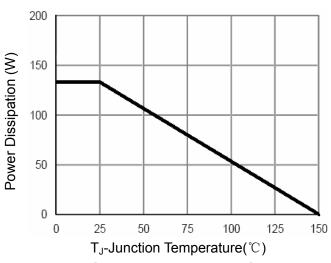
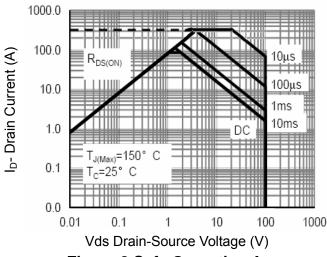


Figure 9 Power De-rating



**Figure 8 Safe Operation Area** 

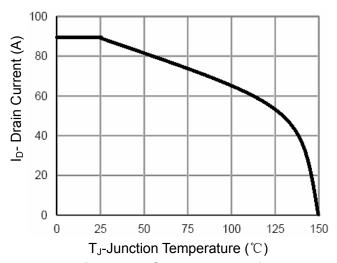


Figure 10 Current De-rating

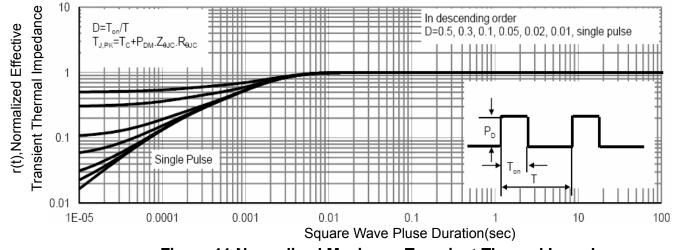
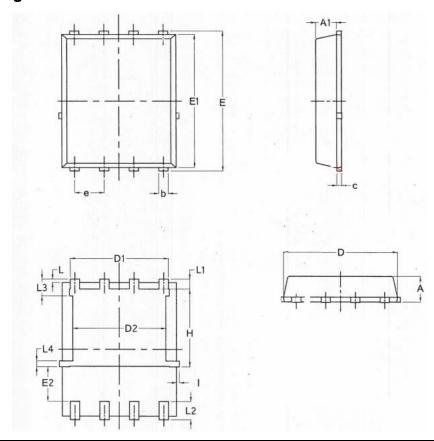


Figure 11 Normalized Maximum Transient Thermal Impedance



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# **DFN5X6-8L Package Information**



| Symbol | Dimensions In Millimeters |          |       | Dimensions In Inches |           |        |  |
|--------|---------------------------|----------|-------|----------------------|-----------|--------|--|
|        | Min.                      | Nom.     | Max.  | Min.                 | Nom.      | Max.   |  |
| Α      | 0.90                      | 1.10     | 1.17  | 0.0354               | 0.0433    | 0.0461 |  |
| A1     | 0.824                     | 0.897    | 0.97  | 0.0324               | 0.0353    | 0.0382 |  |
| b      | 0.33                      | 0.41     | 0.50  | 0.0130               | 0.0161    | 0.0197 |  |
| С      | 0.150                     | 0.20     | 0.250 | 0.0059               | 0.0079    | 0.0098 |  |
| D      | 4.80                      | 4.90     | 5.00  | 0.1890               | 0.1929    | 0.1969 |  |
| D1     | 3.91                      | 4.22     | 4.36  | 0.1539               | 0.1661    | 0.1717 |  |
| D2     | 3.85                      | 4.00     | 4.15  | 0.1516               | 0.1575    | 0.1634 |  |
| E      | 5.90                      | 60.5     | 6.15  | 0.2323               | 0.2382    | 0.2421 |  |
| E1     | 5.65                      | 5.76     | 5.85  | 0.2224               | 0.2268    | 0.2303 |  |
| E2     | 1.10                      | /        | 1     | 0.0433               | 1         | 1      |  |
| е      |                           | 1.27 BSC |       |                      | 0.050 BSC |        |  |
| L      | 0.05                      | 0.15     | 0.25  | 0.0020               | 0.0059    | 0.0098 |  |
| L1     | 0.38                      | 0.425    | 0.50  | 0.0150               | 0.0167    | 0.0197 |  |
| L2     | 0.51                      | 0.785    | 0.86  | 0.0201               | 0.0309    | 0.0339 |  |
| L3     | 0.55                      | 0.70     | 0.85  | 0.0217               | 0.0276    | 0.0335 |  |
| L4     | 0.10                      | 0.25     | 0.40  | 0.0039               | 0.0098    | 0.0157 |  |
| Н      | 3.25                      | 3.35     | 3.58  | 0.1280               | 0.1319    | 0.1409 |  |
| I      | 0                         | 1        | 0.18  | 0                    | 1         | 0.0071 |  |



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